L Number	Hits	Search Text	DB	Time stamp
1	2342	((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/15 13:32
2	2960429	metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/15 13:32
3	1640	(((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/15 13:33
4	231313	protrusions	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/15 13:34
5	49	((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and metal) and protrusions	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/15 13:42
6	2	(("6190949") or ("6096581")).PN.	USPAT; US-PGPUB	2003/08/15 13:42
-	0	(heat adj absorb$3) with insulat$3 with ((non-single or poly or polycrystalline) adj (film or layer)) with recrystalliz$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 11:43
-	2	(heat adj absorb$3) and insulat$3 and ((non-single or poly or polycrystalline) adj (film or layer)) and recrystalliz$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 11:47
-	6766	(heat adj absorb$3) and insulat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:01
-	2	((heat adj absorb$3) and insulat$3) and ((non-single or poly or polycrystalline) adj (film or layer)) and recrystalliz$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 11:48
-	0	((heat adj absorb$3) with metal) and insulat$3 and amorphous and ((non-single or poly or polycrystalline) adj (film or layer)) and recrystalliz$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:04
-	0	((heat adj absorb$3) with metal) and insulat$3 and ((amorphous or non-single or poly or polycrystalline) adj (film or layer)) and recrystalliz$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:05
-	1320	(heat adj absorb$3) with metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:15
-	499	((heat adj absorb$3) with metal) and insulat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:06

4	(((heat adj absorb$3) with metal) and insulat$3) and (non-single or poly or polycrystalline) and recrystalliz$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:08
24	(((heat adj absorb$3) with metal) and insulat$3) and (non-single or poly or polycrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:08
1888852	((heat adj absorb$3 or metal) adj layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:08
13	(heat adj absorb$3 with metal) adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:19
538	(heat adj absorb$3) adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:39
1	(((heat adj absorb$3) adj (layer or film)) same metal) and polycrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:21
0	(((heat adj absorb$3) adj (layer or film)) same metal) and recrystalliz$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:21
105	((heat adj absorb$3) adj (layer or film)) same metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:22
1	((heat adj absorb$3) adj (layer or film)) with tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:39
20154	((heat adj absorb$3 or metal) adj layer or film) and tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 15:18
3477	(((heat adj absorb$3 or metal) adj layer or film) and tft) and polycrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 15:19
2873	((((heat adj absorb$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 15:20
0	(((((heat adj absorb$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat$3) and irradat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 15:21
1208	(((((heat adj absorb$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat$3) and crystalliz$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 15:22

-	628	(((((((heat adj absorb$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat$3) and crystalliz$5) and island$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 15:22
-	615	((((((((heat adj absorb$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat$3) and crystalliz$5) and island$1) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 15:23
-	35	(((((((((heat adj absorb$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat$3) and crystalliz$5) and island$1) and semiconductor) and protrusion$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:12
-	0	irradat$4 with protrusion$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 17:14
-	400	irradiat$4 with protrusion$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 17:23
-	1	(irradiat$4 with protrusion$1) with tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 17:16
-	0	((irradiat$4 with protrusion$1) with tft) with crystalliz$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 17:17
-	0	((irradiat$4 with protrusion$1) with tft) and crystalliz$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 17:17
-	24	irradiat$4 with (protrusion$1 same semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 17:23
-	220	irradiat$4 and (protrusion$1 same semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 17:24
-	0	metal with insulat$3 with amorphous with irradat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:06
-	21	metal and insulat$3 and amorphous and irradat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:07
-	121266	metal adj(layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:08
-	121266	metal adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:09

		3067	(metal adj (layer or film)) and tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:09
-		2727	((metal adj (layer or film)) and tft) and insulat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:09
-		613	(((metal adj (layer or film)) and tft) and insulat$4) and crystalliz$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:11
-		368	(((((metal adj (layer or film)) and tft) and insulat$4) and crystalliz$5) and irradiat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:13
-		53	(((((metal adj (layer or film)) and tft) and insulat$4) and crystalliz$5) and irradiat$4) and (semiconductor adj island)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:13
-		53	((((((metal adj (layer or film)) and tft) and insulat$4) and crystalliz$5) and irradiat$4) and (semiconductor adj island)) and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:14
		0	tft with island$1 with amorphous with crystalliz$5 with irradat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 10:35
-		0	tft and island$1 with amorphous near5 crystalliz$5 with irradat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 10:35
-		0	tft and island$1 and amorphous near5 crystalliz$5 with irradat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 10:36
-		1	tft with island$1 with amorphous near5 crystalliz$5 with irradiat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 10:36
-		0	20010045558.URPN.	USPAT	2002/08/15 15:29
-		0	20010045558.URPN.	USPAT	2002/08/15 15:29
-		2	protrusion$1 with crystalliz$5 adj semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 19:08
-		1	(rough$4 with recrystalliz$5) with hsg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 19:09
-		0	20020036312.URPN.	USPAT	2002/08/15 19:10
-		711	rough$4 same recrystalliz$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 19:12

	Count	Query	Databases	Date/Time
	292	rough$4 with recrystalliz$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 19:46
	8	(rough$4 with recrystalliz$5) with amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 19:14
	0	20020034845.URPN.	USPAT	2002/08/15 19:18
	15	("4411734" | "4737474" | "5089432" | "5121186" | "5147820" | "5147826" | "5298436" | "5326722" | "5418398" | "5441904" | "5514621" | "5604157" | "5614428" | "5652156" | "5712181").PN.	USPAT	2002/08/15 19:23
	2	6017819.URPN.	USPAT	2002/08/15 19:39
	0	20020036312.URPN.	USPAT	2002/08/15 19:45
	5	(rough$4 with recrystalliz$5) with semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 19:47
	1885	((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.	USPAT; US-PGPUB	2003/08/15 13:31
	99764	irradiate or irradiation	USPAT; US-PGPUB	2003/04/06 17:45
	595	(((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)	USPAT; US-PGPUB	2003/04/06 17:46
	1217179	metal	USPAT; US-PGPUB	2003/04/06 17:46
	497	((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal	USPAT; US-PGPUB	2003/04/06 17:46
	622038	channel	USPAT; US-PGPUB	2003/04/06 17:46
	458	(((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal) and channel	USPAT; US-PGPUB	2003/04/06 17:48
	325606	semiconductor	USPAT; US-PGPUB	2003/04/06 17:48
	451	((((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal) and channel) and semiconductor	USPAT; US-PGPUB	2003/04/06 17:48
	661709	protrusion or project or projection	USPAT; US-PGPUB	2003/04/06 17:50
	141	(((((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal) and channel) and semiconductor) and (protrusion or project or projection)	USPAT; US-PGPUB	2003/04/06 17:50
	4	("5581092" | "5959313" | "6281057" | "6323071").PN.	USPAT	2003/04/06 19:12
	0	6506669.URPN.	USPAT	2003/04/06 19:13
	0	6506669.URPN.	USPAT	2003/04/06 19:13